

Edition 1.0 2010-05

PUBLICLY AVAILABLE SPECIFICATION

PRE-STANDARD

Waveguide type dielectric resonators -Part 1-5: General information and test conditions - Measurement method of conductivity at interface between conductor layer and dielectric substrate at microwave frequency

https://standards.itel

720-a870-4844-ae7d-29c439ca0e77/iec-



THIS PUBLICATION IS COPYRIGHT PROTECTED

Copyright © 2010 IEC, Geneva, Switzerland

All rights reserved. Unless otherwise specified, no part of this publication may be reproduced or utilized in any form or by any means, electronic or mechanical, including photocopying and microfilm, without permission in writing from either IEC or IEC's member National Committee in the country of the requester.

If you have any questions about IEC copyright or have an enquiry about obtaining additional rights to this publication, please contact the address below or your local IEC member National Committee for further information.

IEC Central Office 3, rue de Varembé CH-1211 Geneva 20 Switzerland Email: inmail@iec.ch Web: www.iec.ch

About the IEC

The International Electrotechnical Commission (IEC) is the leading global organization that prepares and publishes International Standards for all electrical, electronic and related technologies.

About IEC publications

The technical content of IEC publications is kept under constant review by the IEC. Rease make sure that you have the latest edition, a corrigenda or an amendment might have been published.

Catalogue of IEC publications: <u>www.iec.ch/searchpub</u>

The IEC on-line Catalogue enables you to search by a variety of criteria (reference number, text, technical committee,...). It also gives information on projects, withdrawn and replaced publications

IEC Just Published: www.iec.ch/online_news/justpub

Stay up to date on all new IEC publications. Just Published details twice a month all new publications released. Available on-line and also by email.

Electropedia: <u>www.electropedia.org</u>

The world's leading online dictionary of electronic and electrical terms containing more than 20 000 terms and definitions in English and French, with equivalent terms in additional languages. Also known as the International Electrotechnical Vocabulary online.

• Customer Service Centre: <u>www.iec.ch/webstore/custServ</u> If you wish to give us your feedback on this publication of need further assistance, please visit the Customer Service Centre FAQ or contact us:

Email: csc@iec.ch Tel.: +41 22 919 02 11 Fax: +41 22 919 03 00



Edition 1.0 2010-05

PUBLICLY AVAILABLE SPECIFICATION

PRE-STANDARD

Waveguide type dielectric resonators Part 1-5: General information and test conditions – Measurement method of conductivity at interface between conductor layer and dielectric substrate at microwave frequency.

https://standards.iteh

720-a870-4844-ae7d-29c439ca0e77/iec-

INTERNATIONAL ELECTROTECHNICAL COMMISSION

PRICE CODE

R

ICS 31.140

ISBN 978-2-88910-935-7

CONTENTS

FO	REWORD	4	
ΙΝΤ	RODUCTION	6	
1	Scope	7	
2	Normative references	8	
3	Measurement and related parameters		
4	Calculation equations for R_i and σ_i	9	
5	Preparation of specimen		
6	Measurement equipment and apparatus	.13	
	6.1 Measurement equipment	-	
	6.2 Measurement apparatus	.13	
7	Measurement procedure		
	7.1 Set up of measurement equipment and apparatus		
	7.2 Measurement of reference level		
	7.3 Measurement procedure of Q,		
	7.4 Determination of σ_i and measurement uncertainty	. 16	
8	Example of measurement result		
Anr	nex A (informative) Derivation of equation (4) for R_i	. 18	
Anr	nex B (informative) Calculation uncertainty of parameters in Figure 3	. 19	
	liography		
	A S 133-1-5-2010		
Figu and	ure 1 – Surface resistance R_s , surface conductivity σ_s , interface resistance R_i , interface conductivity σ_i .	7	
	ure 2 – The TE _{01δ} mode dielectric rod resonator to measure σ_i	9	
Figu Cal	ure 3 – Parameters chart of f_0 , g , P_{rod} and P_{sub} for reference sapphire rod. culation conditions: ε'_{rod} = 9.4, d = 10.00 mm and h = 5.00 mm	.11	
	ure 4 – Parameters chart of f_0 , g, P_{rod} and P_{sub} for reference (Zr,Sn)TiO ₄ rod.		
	culation conditions: $\varepsilon'_{rod} = 39$, $d = 14.00$ mm and $h = 6.46$ mm	. 12	
Figu	ure 5 – Schematic diagram of measurement equipments	. 13	
Figu	ure 6 – Schematic diagram of measurement apparatus for $\sigma_{_{ri}}$. 14	
	ure 7 – Frequency response for reference sapphire rod with two dielectric strates as shown in figure 2	. 15	
Figu	ure 8 – Resonance frequency $f_{ m 0}$, insertion attenuation $I\!A_{ m 0}$ and half-power band		
wid	th f_{BW}	.16	
Tab	le 1 – Specifications of reference rods.	. 10	
Tab	le 2 – ε'_{rod} and $ an \delta_{rod}$ of reference rods measured by the method (IEC 61338-1-3)	. 16	
	le 3 – \mathcal{E}'_{sub} and $\tan \delta_{sub}$ of a LTCC test substrate measured by the method C 61338-1-4).	. 17	

Table 4 – Measurement results of σ_i and σ_{ri} of a copper layer in LTCC substrate with	
\mathcal{E}'_{sub} =4.76, <i>d</i> '=45 mm and <i>t</i> =0.415 mm	17
Table B.1 – Parameters obtained by FEM and rigorous analysis (IEC61338-1-3) for the TE_{011} mode resonator with ε'_{rod} =9.4, d=10.0 mm, and h=5.0 mm	19
Table B.2 – Calculated parameters $f_{_0}$, g , $P_{_{rod}}$, $P_{_{sub}}$, $R_{_i}$, $\sigma_{_i}$ and $\sigma_{_{ri}}$ for the ${ m TE}_{_{01\delta}}$	
mode resonator with \mathcal{E}'_{rod} =9.4 and 9.3, with the test condition of \mathcal{E}'_{sub} =6.0,	



INTERNATIONAL ELECTROTECHNICAL COMMISSION

WAVEGUIDE TYPE DIELECTRIC RESONATORS -

Part 1-5: General information and test conditions – Measurement method of conductivity at interface between conductor layer and dielectric substrate at microwave frequency

FOREWORD

- 1) The International Electrotechnical Commission (IEC) is a worldwide organization for standardization comprising all national electrotechnical committees (IEC National Committees). The object of IEC is to promote international co-operation on all questions concerning standardization in the electrical and electronic fields. To this end and in addition to other activities, IEC publishes International Standards, Technical Specifications, Technical Reports, Publicly Available Specifications (PAS) and Guides (hereafter referred to as "IEC Publication(s)"). Their preparation is entrusted to technical committees; any IEC National Committee interested in the subject dealt with may participate in this preparatory work. International, governmental and non-governmental organizations liaising with the IEC also participate in this preparation. IEC collaborates closely with the International Organization for Standardization (ISO) in accordance with conditions determined by agreement between the two organizations.
- 2) The formal decisions or agreements of IEC on technical matters express, as nearly as possible, an international consensus of opinion on the relevant subjects since each technical committee has representation from all interested IEC National Committees.
- 3) IEC Publications have the form of recommendations for international use and are accepted by IEC National Committees in that sense. While all reasonable efforts are made to ensure that the technical content of IEC Publications is accurate, IEC cannot be hald responsible for the way in which they are used or for any misinterpretation by any end user.
- 4) In order to promote international uniformity, IEC National Committees undertake to apply IEC Publications transparently to the maximum extent possible in their national and regional publications. Any divergence between any IEC Publication and the corresponding national or regional publication shall be clearly indicated in the latter.
- 5) IEC itself does not provide any attestation of conformity Independent certification bodies provide conformity assessment services and, in some areas, access to IEC marks of conformity. IEC is not responsible for any services carried out by independent certification bodies.
- 6) All users should ensure that they have the latest edition of this publication.
- 7) No liability shall attach to IEC or its directors, employees, servants or agents including individual experts and members of its technical committees and IEC National Committees for any personal injury, property damage or other damage of any nature whatsoever, whether direct or indirect, or for costs (including legal fees) and expenses arising out of the publication, use of, or reliance upon, this IEC Publication or any other IEC Publications
- 8) Attention is drawn to the Normative references cited in this publication. Use of the referenced publications is indispensable for the correct application of this publication.

A PAS is a technical specification not fulfilling the requirements for a standard, but made available to the public.

IEC/PAS 61338-1-5 has been processed by IEC technical committee 49: Piezoelectric and dielectric devices for frequency control and selection.

The text of this PAS is based on the following document:	This PAS was approved for publication by the P-members of the committee concerned as indicated in the following document
Draft PAS	Report on voting
49/873/PAS	49/902/RVD

Following publication of this PAS, which is a pre-standard publication, the technical committee or subcommittee concerned may transform it into an International Standard.

This PAS shall remain valid for an initial maximum period of 3 years starting from the publication date. The validity may be extended for a single period up to a maximum of 3 years,

at the end of which it shall be published as another type of normative document, or shall be withdrawn.

A list of all parts of IEC 61338 series under the general title *Waveguide type dielectric resonators* can be found on the IEC website.

IEC 61338 consists of the following parts, under the general title *Waveguide type dielectric resonators*:

- Part 1: Generic specification
- Part 1-3: General information and test conditions Measurement method of complex relative permittivity for dielectric resonator materials at microwave frequency
- Part 1-4: General information and test conditions Measurement method of complex relative permittivity for dielectric resonator materials at millimeter-wave frequency
- Part 2: Guidelines for oscillator and filter applications
- Part 4: Sectional specification
- Part 4-1: Blank detail specification

tps://standards.iteh.ai

INTRODUCTION

The International Electrotechnical Commission (IEC) draws attention to the fact that it is claimed that compliance with this PAS may involve the use of a patent concerning:

"Measurement method of conductivity at interface of conductor layer"

"Measurement method of conductivity of conductor layer"

IEC takes no position concerning the evidence, validity and scope of this patent right.

The holder of this patent right has assured the IEC that he/she is willing to negotiate licences under reasonable and non-discriminatory terms and conditions with applicants throughout the world. In this respect, the statement of the holder of this patent right is registered with IEC. Information may be obtained from:

KYOCERA Corporation

6 Takeda Tobadono-cho, Fushimiku, Kyoto 612-5801, Japan

Attention is drawn to the possibility that some of the elements of this PAS may be the subject of patent rights other than those identified above. IEC shall not be held responsible for identifying any or all such patent rights.

ISO (www.iso.org/patents) and IEC (http://www.iec.ch/tctools/patent_decl.htm) maintain online data bases of patents relevant to their standards. Users are encouraged to consult the data bases for the most up to date information concerning patents.

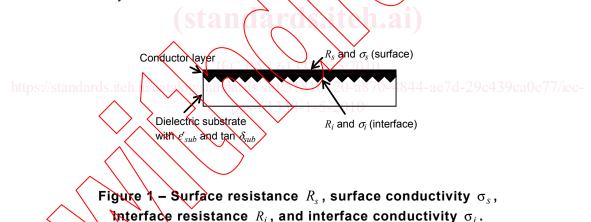
WAVEGUIDE TYPE DIELECTRIC RESONATORS -

Part 1-5: General information and test conditions – Measurement method of conductivity at interface between conductor layer and dielectric substrate at microwave frequency

1 Scope

Microwave circuits are popularly formed on multi-layered organic or non-organic substrates. In the microwave circuits, the attenuation of planar transmission lines such as striplines, microstrip lines, and coplanar lines are determined by their conductor loss, dielectric loss and radiation loss. Among them, the conductor loss is a major factor in the attenuation of the planar transmission lines. A new measurement method is needed to evaluate the conductivity of transmission line on or in the substrates such as the organic, ceramic and LTCC (low temperature co-fired ceramics) substrates.

The IEC 61338-1-3 described the measurement method for the surface resistance R_s and effective conductivity σ on the surface of the conductor. The term σ is designated as σ_s in this PAS, and is called surface conductivity (Figure 1). (This PAS describes a measurement method for resistance and effective conductivity at the interface between conductor layer and dielectric substrate designated as R_i and σ_r respectively, and are called interface resistance and interface conductivity.



For the transmission line in the substrates, the electric current is concentrated at the interface between conductor layer and dielectric substrate, because the skin depth δ in the conductor is the order of μ m in thickness at the microwave frequencies. In microstrip lines, the current is concentrated at the interface, rather than at the open face of the conductor. Furthermore, in copper-clad organic substrates, the interface side of the copper foil has rugged structure to hold the strong adhesive strength. In LTCC substrates, the interface between the conductor and ceramics has a rough structure, depending on the co-firing process and the material compositions. The interface conditions increase the conductor loss. Therefore, the evaluation of R_i and σ_i is important to design microwave circuit and to improve the conductor fabrication process.

This measurement method has the following characteristics:

- the interface resistance R_i is obtained by measuring the resonant frequency f_0 and unloaded quality factor Q_u of a $\text{TE}_{01\delta}$ mode dielectric rod resonator shown in Figure 2;

(1)

- the interface conductivity σ_i and the relative interface conductivity $\sigma_{ri} = \sigma_i / \sigma_0$ are calculated from the measured R_i value, where $\sigma_0 = 5.8 \times 10^7$ S/m is the conductivity of standard copper;

- 8 -

– the measurement uncertainty of σ_{ri} ($\Delta\sigma_{ri}$) is less than 5%.

2 Normative references

The following referenced documents are indispensable for the application of this PAS. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 61338-1-3: Waveguide type dielectric resonators - Part 1-3: General information and test conditions – Measurement method of complex relative permittivity for dielectric resonator materials at microwave frequency

IEC 61338-1-4: Waveguide type dielectric resonators - Part 1-4: General information and test conditions – Measurement method of complex relative permittivity for dielectric resonator materials at millimetre-wave frequency

3 Measurement and related parameters

The relationship between R_s and σ_s is given by

$$R_s = \sqrt{\frac{\pi f_0 \mu}{\sigma_s}}$$
 , σ_s

where

 $R_{\rm s}$ is the surface resistance;

- f_0 is the resonance frequency;
- μ is the permeability of the conductor;
- $\sigma_{\rm s}$ is the surface conductivity:
- σ_{rs} is the relative surface conductivity.

Particularly, μ equals μ_0 ($\mu_0 = 4\pi \times 10^{-7}$ H/m) for nonmagnetic conductors such as copper and silver.

The relationship between R_i and σ_i is given by

$$R_i = \sqrt{\frac{\pi f_0 \mu}{\sigma_i}} \quad , \quad \sigma_i = \sigma_{ri} \sigma_0 \tag{2}$$

where

 R_i is the interface resistance;

 σ_i is the interface conductivity;

 σ_{ri} is the relative interface conductivity.

The skin depth $\,\delta\,$ is given by

$$\delta = \sqrt{\frac{1}{\pi f \mu \sigma}} \tag{3}$$

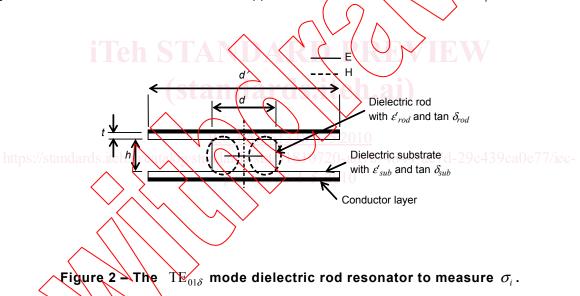
PAS 61338-1-5 © IEC:2010(E)

- f is the frequency;
- σ is the conductivity of the conductor.

To obtain high accuracy in this measurement method, the σ_{ri} of the conductor is preferable to be higher than 5%, and the thickness of conductor to be three times greater than skin depth δ . The measurement frequencies are limited to be 5 GHz and 13 GHz in this PAS because of the reference dielectric rods used in this PAS.

4 Calculation equations for R_i and σ_i

Figure 2 shows the structure of a $\text{TE}_{01\delta}$ mode dielectric rod resonator for the R_i measurement. The resonator consists of a dielectric rod and a pair of dielectric substrates with a conductor layer at one side. The dielectric rod has diameter d_i , height h_i , relative permittivity ε'_{rod} , and loss tangent $\tan \delta_{rod}$. The pair of dielectric substrates have the same values of diameter d'_i , thickness t_i , relative permittivity ε'_{sub} and loss tangent $\tan \delta_{sub}$. To suppress the radiation loss, the diameter d'_i shall be three times greater than d. The conductor layers on each dielectric substrate are supposed to have the same value of R_i .



In this structure, the conductive loss of the $\text{TE}_{01\delta}$ mode resonator is caused by the interface resistance R_i . The value of $1/Q_u$ is given by a sum of power losses due to R_i , $\tan \delta_{rod}$ and $\tan \delta_{sub}$:

$$\frac{1}{Q_u} = \frac{R_i}{g} + P_{rod} \tan \delta_{rod} + P_{sub} \tan \delta_{sub} , \qquad (4)$$

where

 $\begin{array}{ll}g & \quad \text{is the geometric factor of the resonator (Ω);}\\ P_{rod} & \quad \text{is the partial electric energy filling factor of the dielectric rod;}\\ P_{sub} & \quad \text{is the partial electric energy filling factor of the dielectric substrate.} \end{array}$